

# Low Offset, Low Noise, RRO Operational Amplifier

Check for Samples: SM73308

### **FEATURES**

(Unless Otherwise Noted, Typical Values at  $V_S$  = 2.7V)

- Renewable Energy Grade
- Ensured 2.7V and 5V Specifications
- Maximum V<sub>OS</sub> 850µV (Limit)
- Voltage noiseN
  - $f = 100 \text{ Hz} 12.5 \text{ nV}/\sqrt{\text{Hz}}$
  - f = 10 kHz 7.5nV/√Hz
- Rail-to-Rail Output Swing
  - $R_L = 600\Omega$  100mV From Rail
  - $R_L = 2k\Omega 50mV$  From Rail
- Open Loop Gain With  $R_L = 2k\Omega \ 100dB$
- V<sub>CM</sub> 0 to V<sup>+</sup> -0.9V
- Supply Current 550μA
- Gain Bandwidth Product 3.5MHz
- Temperature Range -40°C to 125°C

#### **APPLICATIONS**

- Transducer Amplifier
- Instrumentation Amplifier
- Precision Current Sensing
- Data Acquisition Systems
- Active Filters and Buffers
- Sample and Hold
- Portable/battery Powered Electronics
- Automotive

#### **Connection Diagram**

#### DESCRIPTION

The SM73308 is a single low noise precision operational amplifier intended for use in a wide range of applications. Other important characteristics include: an extended operating temperature range of -40°C to 125°C, the tiny SC70-5 package, and low input bias current.

The extended temperature range of −40°C to 125°C allows the SM73308 to accommodate a broad range of applications. The SM73308 expands Tl's Silicon Dust™ amplifier portfolio offering enhancements in size, speed, and power savings. The SM73308 is ensured to operate over the voltage range of 2.7V to 5.0V and has rail-to-rail output.

The SM73308 is designed for precision, low noise, low voltage, and miniature systems. This amplifier provides rail-to-rail output swing into heavy loads. The maximum input offset is 850  $\mu$ V at room temperature and the input common mode voltage range includes ground.

The SM73308 is offered in the tiny SC70-5 package.

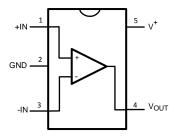


Figure 1. SC70-5 – Top View See Package Number DCK

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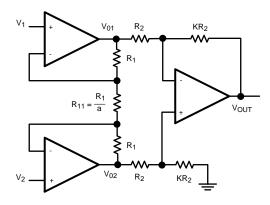
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#### Instrumentation Amplifier



 $V_0 = -K (2a + 1) (V_1 - V_2)$ (1)



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

# Absolute Maximum Ratings (1)(2)

Absolute Maximum Nathing				
	Machine Model	200V		
ESD Tolerance <sup>(3)</sup>	Human Body Model	2000V		
Differential Input Voltage		± Supply Voltage		
Voltage at Input Pins		$(V^{+}) + 0.3V, (V^{-}) - 0.3V$		
Current at Input Pins		±10 mA		
Supply Voltage (V <sup>+</sup> –V ¯)		5.75\		
Output Short Circuit to V+		See <sup>(4)</sup>		
Output Short Circuit to V		See <sup>(5)</sup>		
Mounting Temperture	Infrared or Convection (20 sec)	235°C		
	Wave Soldering Lead Temp (10 sec)	260°C		
Storage Temperature Range		−65°C to 150°C		
Junction Temperature (6)		150°C		

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- Human Body Model is 1.5 k $\Omega$  in series with 100 pF. Machine Model is  $0\Omega$  in series with 20 pF.
- Shorting output to V<sup>+</sup> will adversely affect reliability. Shorting output to V<sup>-</sup> will adversely affect reliability.
- The maximum power dissipation is a function of  $T_{J(MAX)}$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation at any ambient temperature is  $P_D = (T_{J(MAX)} T_A) I \theta_{JA}$ . All numbers apply for packages soldered directly into a PC board.

# Operating Ratings<sup>(1)</sup>

Supply Voltage	2.7V to 5.5V
Temperature Range	−40°C to 125°C
Thermal Resistance (θ <sub>JA</sub> )	440 °C/W

Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.



# 2.7V DC Electrical Characteristics(1)

Unless otherwise specified, all limits are ensured for  $T_A = 25$  °C.  $V^+ = 2.7V$ ,  $V^- = 0V$ ,  $V_{CM} = V^+/2$ ,  $V_O = V^+/2$  and  $R_L > 1M\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Condition	Min <sup>(2)</sup>	Typ <sup>(3)</sup>	Max <sup>(2)</sup>	Units	
V <sub>OS</sub>	Input Offset Voltage			0.3	0.85 <b>1.0</b>	mV	
TCV <sub>OS</sub>	Input Offset Voltage Average Drift			-0.45		μV/°C	
I <sub>B</sub>	Input Bias Current <sup>(4)</sup>	V <sub>CM</sub> = 1V		-0.1	100 <b>250</b>	pA	
los	Input Offset Current <sup>(4)</sup>			0.004	100	pA	
Is	Supply Current			550	900 <b>910</b>	μA	
CMRR	Common Mode Rejection Ratio	0.5 ≤ V <sub>CM</sub> ≤ 1.2V	74 <b>72</b>	80		dB	
PSSR	Power Supply Rejection Ratio	2.7V ≤ V <sup>+</sup> ≤ 5V	82 <b>76</b>	90		dB	
V <sub>CM</sub>	Input Common-Mode Voltage Range	For CMRR ≥ 50dB	0		1.8	V	
	Laura Cina I Vallana Caia (5)	$R_L = 600\Omega$ to 1.35V, $V_O = 0.2V$ to 2.5V	92 <b>80</b>	100		-ID	
A <sub>V</sub>	Large Signal Voltage Gain (5)	$R_L = 2k\Omega \text{ to } 1.35V,$ $V_O = 0.2V \text{ to } 2.5V$	98 <b>86</b>	100		dB	
.,	0.1.10.1	$R_L = 600\Omega$ to 1.35V $V_{IN} = \pm 100$ mV	0.11 <b>0.14</b>	0.084 to 2.62	2.59 <b>2.56</b>	.,	
Vo	Output Swing	$R_L = 2k\Omega$ to 1.35V V <sub>IN</sub> = ± 100mV	0.05 <b>0.06</b>	0.026 to 2.68	2.65 <b>2.64</b>	V	
1	Output Chart Circuit Current	Sourcing, $V_O = 0V$ $V_{IN} = 100 \text{mV}$	18 <b>11</b>	24		A	
l <sub>O</sub>	Output Short Circuit Current	Sinking, $V_O = 2.7V$ $V_{IN} = -100 \text{mV}$	18 <b>11</b>	22		mA	

<sup>(1)</sup> Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T<sub>J</sub> = T<sub>A</sub>.

# 2.7V AC Electrical Characteristics<sup>(1)</sup>

Unless otherwise specified, all limits are ensured for  $T_A = 25$ °C.  $V^+ = 5.0V$ ,  $V^- = 0V$ ,  $V_{CM} = V^+/2$ ,  $V_O = V^+/2$  and  $R_L > 1M\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min <sup>(2)</sup>	Typ <sup>(3)</sup>	Max <sup>(2)</sup>	Units
SR	Slew Rate <sup>(4)</sup>	$A_V = +1$ , $R_L = 10 \text{ k}\Omega$		1.4		V/µs
GBW	Gain-Bandwidth Product			3.5		MHz
$\Phi_{m}$	Phase Margin			79		Deg
G <sub>m</sub>	Gain Margin			-15		dB
e <sub>n</sub>	Input-Referred Voltage Noise (Flatband)	f = 10kHz		7.5		nV/√Hz
e <sub>n</sub>	Input-Referred Voltage Noise (I/f)	f = 100Hz		12.5		nV/√ <del>Hz</del>
in	Input-Referred Current Noise	f = 1kHz		0.001		pA/√Hz
THD	Total Harmonic Distortion	$f = 1kHz, A_V = +1$ $R_L = 600\Omega, V_{IN} = 1 V_{PP}$		0.007		%

<sup>(1)</sup> Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T<sub>J</sub> = T<sub>A</sub>.

<sup>(2)</sup> All limits are ensured by testing or statistical analysis.

<sup>(3)</sup> Typical values represent the most likely parametric norm.

<sup>(4)</sup> Limits ensured by design.

<sup>(5)</sup>  $R_L$  is connected to mid-supply. The output voltage is set at 200mV from the rails.  $V_O = GND + 0.2V$  and  $V_O = V^+ - 0.2V$ 

<sup>(2)</sup> All limits are ensured by testing or statistical analysis.

<sup>(3)</sup> Typical values represent the most likely parametric norm.

<sup>(4)</sup> The number specified is the slower of positive and negative slew rates.



# 5.0V DC Electrical Characteristics (1)

Unless otherwise specified, all limits are ensured for  $T_A = 25^{\circ}C$ .  $V^+ = 5.0V$ ,  $V^- = 0V$ ,  $V_{CM} = V^+/2$ ,  $V_O = V^+/2$  and  $R_L > 1M\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Condition	Min <sup>(2)</sup>	Typ <sup>(3)</sup>	Max <sup>(2)</sup>	Units	
V <sub>OS</sub>	Input Offset Voltage			0.25	0.85 <b>1.0</b>	mV	
TCV <sub>OS</sub>	Input Offset Voltage Average Drift			-0.35		μV/°C	
I <sub>B</sub>	Input Bias Current <sup>(4)</sup>	V <sub>CM</sub> = 1V		-0.23	100 <b>250</b>	pА	
I <sub>OS</sub>	Input Offset Current <sup>(4)</sup>			0.017	100	pА	
Is	Supply Current			600	950 <b>960</b>	μA	
CMRR	Common Mode Rejection Ratio	0.5 ≤ V <sub>CM</sub> ≤ 3.5V	80 <b>79</b>	90		dB	
PSRR	Power Supply Rejection Ratio	2.7V ≤ V <sup>+</sup> ≤ 5V	82 <b>76</b>	90		dB	
V <sub>CM</sub>	Input Common-Mode Voltage Range	For CMRR ≥ 50dB	0		4.1	V	
^	Laura Cianal Valtara Caia (5)	$R_L = 600\Omega$ to 2.5V, V <sub>O</sub> = 0.2V to 4.8V	92 <b>89</b>	100		40	
A <sub>V</sub>	Large Signal Voltage Gain <sup>(5)</sup>	$R_L = 2k\Omega \text{ to } 2.5V,$ $V_O = 0.2V \text{ to } 4.8V$	98 <b>95</b>	100		dB	
	Outside Outside	$R_L = 600\Omega$ to 2.5V $V_{IN} = \pm 100$ mV	0.15 <b>0.23</b>	0.112 to 4.9	4.85 <b>4.77</b>	.,	
V <sub>O</sub> Output Swing	Output Swing	$R_L = 2k\Omega$ to 2.5V V <sub>IN</sub> = ± 100mV	0.06 <b>0.07</b>	0.035 to 4.97	4.94 <b>4.93</b>	V	
lo	Output Chart Circuit Current (4) (6)	Sourcing, $V_O = 0V$ $V_{IN} = 100 \text{mV}$	35 <b>35</b>	75		A	
	Output Short Circuit Current (4) (6)	Sinking, $V_0 = 2.7V$ $V_{IN} = -100 \text{mV}$	35 <b>35</b>	66		mA	

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that  $T_J = T_A$ .
- All limits are ensured by testing or statistical analysis.
- (3) Typical values represent the most likely parametric norm.
- (4) Limits ensured by design.
- $R_L$  is connected to mid-supply. The output voltage is set at 200mV from the rails.  $V_O = GND + 0.2V$  and  $V_O = V^+ 0.2V$  Continuous operation of the device with an output short circuit current larger than 35mA may cause permanent damage to the device.

# 5.0V AC Electrical Characteristics(1)

Unless otherwise specified, all limits are ensured for  $T_A = 25$  °C.  $V^+ = 5.0 V$ ,  $V^- = 0 V$ ,  $V_{CM} = V^+/2$ ,  $V_O = V^+/2$  and  $R_L > 1 M\Omega$ . Boldface limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min <sup>(2)</sup>	Typ <sup>(3)</sup>	Max <sup>(2)</sup>	Units
SR	Slew Rate (4)	$A_V = +1$ , $R_L = 10 \text{ k}\Omega$		1.4		V/µs
GBW	Gain-Bandwidth Product			3.5		MHz
$\Phi_{m}$	Phase Margin			79		Deg
G <sub>m</sub>	Gain Margin			-15		dB
e <sub>n</sub>	Input-Referred Voltage Noise (Flatband)	f = 10kHz		6.5		nV/√ <del>Hz</del>
e <sub>n</sub>	Input-Referred Voltage Noise (I/f)	f = 100Hz		12		nV/√ <del>Hz</del>
i <sub>n</sub>	Input-Referred Current Noise	f = 1kHz		0.001		pA/√ <del>Hz</del>
THD	Total Harmonic Distortion	$ f = 1kHz, A_V = +1 $ $R_L = 600\Omega, V_{IN} = 1 V_{PP} $		0.007		%

- Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that  $T_J = T_A$ .
- All limits are ensured by testing or statistical analysis.
- Typical values represent the most likely parametric norm.
- The number specified is the slower of positive and negative slew rates.



# **Typical Performance Characteristics**

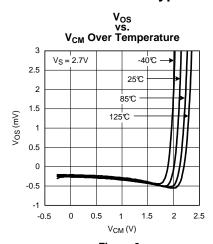


Figure 2.

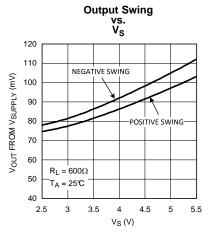
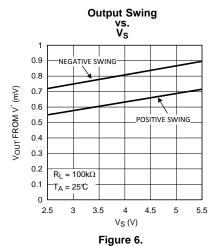


Figure 4.



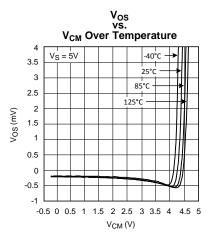


Figure 3.

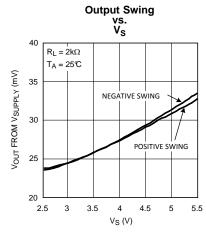


Figure 5.

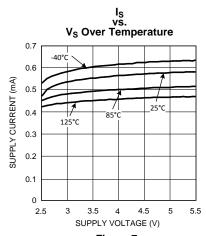


Figure 7.





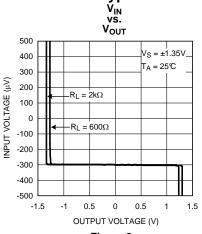


Figure 8.

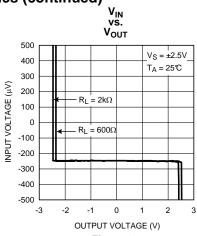


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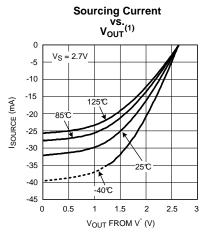


Figure 10.

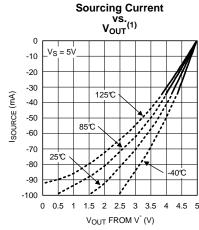
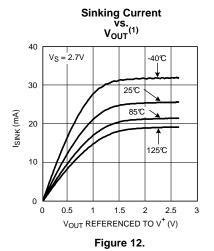


Figure 11.



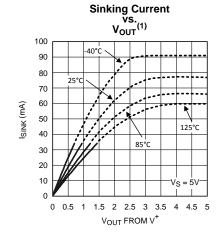


Figure 13.

(1) Continuous operation of the device with an output short circuit current larger than 35mA may cause permanent damage to the device.



# **Typical Performance Characteristics (continued)**

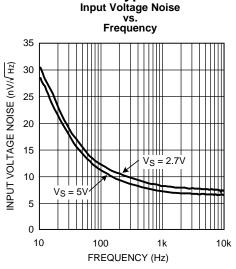
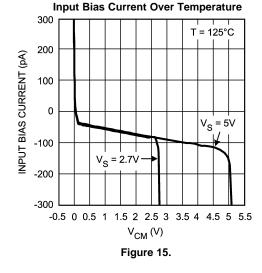


Figure 14.



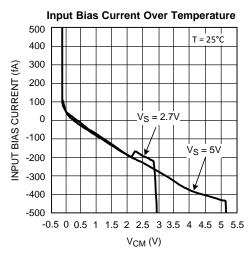


Figure 16. THD+N

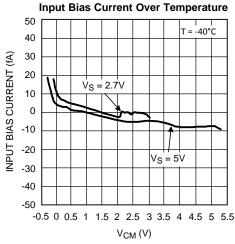


Figure 17.

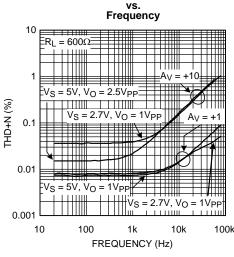


Figure 18.

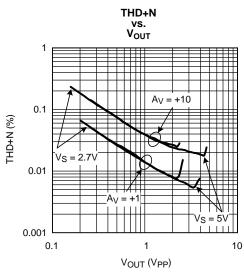
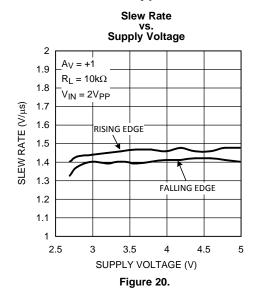
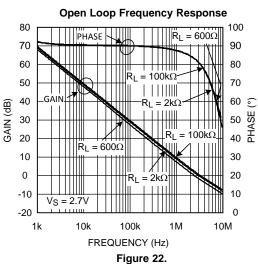


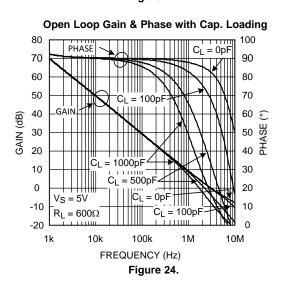
Figure 19.

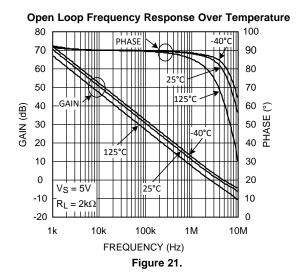


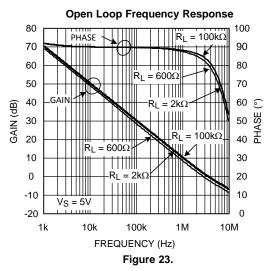
# **Typical Performance Characteristics (continued)**

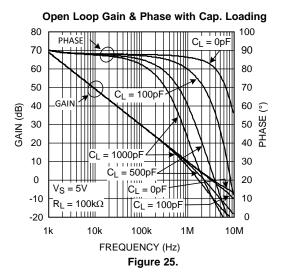






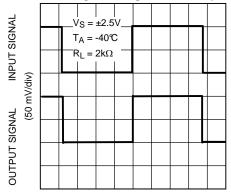








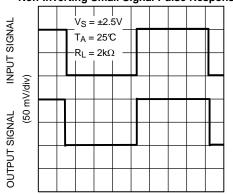
# Typical Performance Characteristics (continued) Non-Inverting Small Signal Pulse Response Non-Inverting Large



TIME (10 µs/div)

Figure 26.

## Non-Inverting Small Signal Pulse Response



TIME (10 µs/div)

Figure 28.

#### Non-Inverting Small Signal Pulse Response

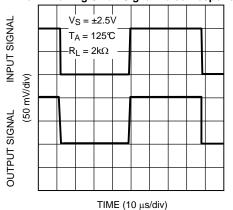
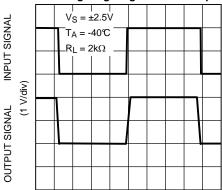


Figure 30.

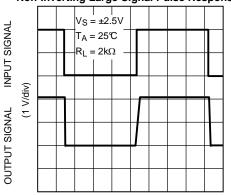
Non-Inverting Large Signal Pulse Response



TIME (10 µs/div)

Figure 27.

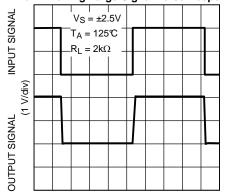
#### Non-Inverting Large Signal Pulse Response



TIME (10 µs/div)

Figure 29.

#### Non-Inverting Large Signal Pulse Response

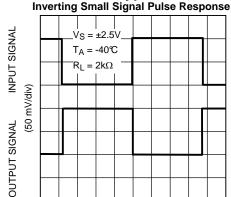


TIME (10 µs/div)

Figure 31.



# Typical Performance Characteristics (continued) Inverting Small Signal Pulse Response Inverting Large Signal Pulse Response



TIME (10  $\mu$ s/div)

Figure 32.

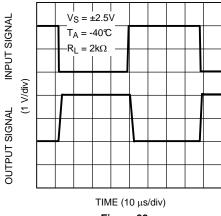
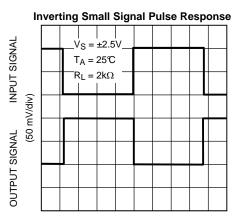


Figure 33.



TIME (10 µs/div)

Figure 34.

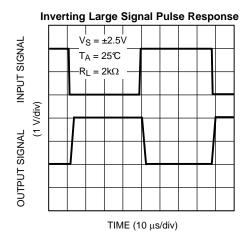
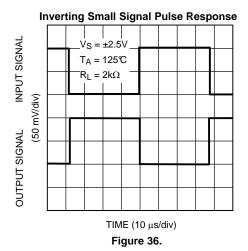


Figure 35.



Inverting Large Signal Pulse Response

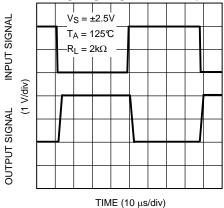


Figure 37.



# Typical Performance Characteristics (continued) Stability

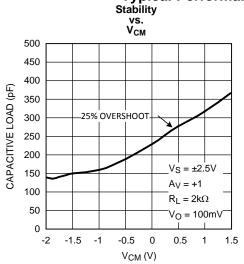
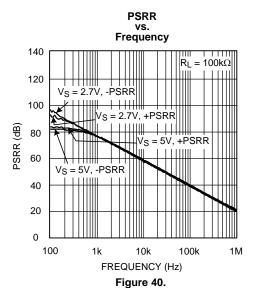


Figure 38.



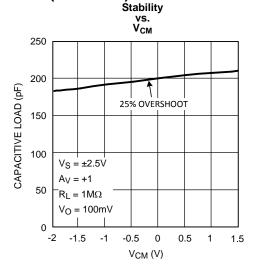


Figure 39.

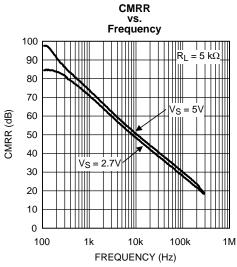


Figure 41.



#### **APPLICATION NOTE**

#### SM73308

The SM73308 is a precision amplifier with very low noise and ultra low offset voltage. SM73308's extended temperature range of −40°C to 125°C enables the user to design a variety of applications including automotive.

The SM73308 has a maximum offset voltage of 1mV over the extended temperature range. This makes the SM73308 ideal for applications where precision is important.

#### **INSTRUMENTATION AMPLIFIER**

Measurement of very small signals with an amplifier requires close attention to the input impedance of the amplifier, gain of the overall signal on the inputs, and the gain on each input since we are only interested in the difference of the two inputs and the common signal is considered noise. A classic solution is an instrumentation amplifier. Instrumentation amplifiers have a finite, accurate, and stable gain. Also they have extremely high input impedances and very low output impedances. Finally they have an extremely high CMRR so that the amplifier can only respond to the differential signal. A typical instrumentation amplifier is shown in Figure 42.

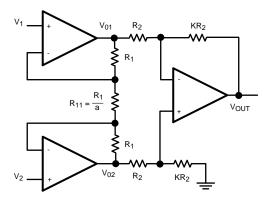


Figure 42. Instrumentation Amplifier

There are two stages in this amplifier. The last stage, output stage, is a differential amplifier. In an ideal case the two amplifiers of the first stage, input stage, would be set up as buffers to isolate the inputs. However they cannot be connected as followers because of real amplifier's mismatch. That is why there is a balancing resistor between the two. The product of the two stages of gain will give the gain of the instrumentation amplifier. Ideally, the CMRR should be infinite. However the output stage has a small non-zero common mode gain which results from resistor mismatch.

In the input stage of the circuit, current is the same across all resistors. This is due to the high input impedance and low input bias current of the SM73308. With the node equations we have:

$$GIVEN: I_{R_1} = I_{R_{11}}$$
 (2)

By Ohm's Law:

$$V_{O1} - V_{O2} = (2R_1 + R_{11}) I_{R_{11}}$$

$$= (2a + 1) R_{11} \cdot I_{R_{11}}$$

$$= (2a + 1) V_{R_{11}}$$
(3)

However:

$$V_{R_{11}} = V_1 - V_2$$
 (4)

So we have:

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$$V_{O1} - V_{O2} = (2a + 1)(V_1 - V_2)$$
 (5)

Now looking at the output of the instrumentation amplifier:

$$V_{O} = \frac{KR_{2}}{R_{2}} (V_{O2} - V_{O1})$$

$$= -K (V_{O1} - V_{O2})$$
(6)

Substituting from Equation 5:

$$V_0 = -K (2a + 1) (V_1 - V_2)$$
 (7)

This shows the gain of the instrumentation amplifier to be:

$$-K(2a+1)$$
 (8)

Typical values for this circuit can be obtained by setting: a = 12 and K= 4. This results in an overall gain of −100.

Figure 43 shows typical CMRR characteristics of this Instrumentation amplifier over frequency. Three SM73308 amplifiers are used along with 1% resistors to minimize resistor mismatch. Resistors used to build the circuit are:  $R_1 = 21.6k\Omega$ ,  $R_{11} = 1.8k\Omega$ ,  $R_2 = 2.5k\Omega$  with K = 40 and a = 12. This results in an overall gain of -1000, -K(2a+1) = -1000.

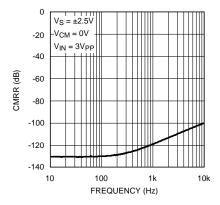


Figure 43. CMRR vs. Frequency

#### **ACTIVE FILTER**

Active filters are circuits with amplifiers, resistors, and capacitors. The use of amplifiers instead of inductors, which are used in passive filters, enhances the circuit performance while reducing the size and complexity of the filter

The simplest active filters are designed using an inverting op amp configuration where at least one reactive element has been added to the configuration. This means that the op amp will provide "frequency-dependent" amplification, since reactive elements are frequency dependent devices.

#### **LOW PASS FILTER**

The following shows a very simple low pass filter.

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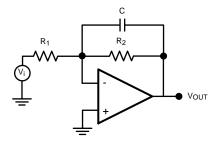


Figure 44. Lowpass Filter

The transfer function can be expressed as follows:

By KCL:

$$\frac{-v_1}{R_1} - \frac{v_0}{\left[\frac{1}{jwc}\right]} - \frac{v_0}{R_2} = 0 \tag{9}$$

Simplifying this further results in:

$$V_{O} = \frac{-R_{2}}{R_{1}} \left[ \frac{1}{\text{jwcR}_{2} + 1} \right] V_{i}$$
 (10)

or

$$\frac{V_O}{V_i} = \frac{-R_2}{R_1} \left[ \frac{1}{jwcR_2 + 1} \right] \tag{11}$$

Now, substituting  $\omega=2\pi f$ , so that the calculations are in f(Hz) and not  $\omega$ (rad/s), and setting the DC gain H<sub>O</sub> =  $-R_2/R_1$  and H =  $V_O/V_i$ 

$$H = H_O \left[ \frac{1}{j2\pi f c R_2 + 1} \right]$$

$$\tag{12}$$

Set:  $f_0 = 1/(2\pi R_1 C)$ 

$$H = H_O\left[\frac{1}{1+j(f/f_O)}\right]$$
(13)

Low pass filters are known as lossy integrators because they only behave as an integrator at higher frequencies. Just by looking at the transfer function one can predict the general form of the bode plot. When the  $f/f_0$  ratio is small, the capacitor is in effect an open circuit and the amplifier behaves at a set DC gain. Starting at  $f_0$ , -3dB corner, the capacitor will have the dominant impedance and hence the circuit will behave as an integrator and the signal will be attenuated and eventually cut. The bode plot for this filter is shown in the following picture:

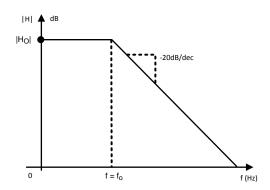


Figure 45. Lowpass Filter Transfer Function

#### **HIGH PASS FILTER**

In a similar approach, one can derive the transfer function of a high pass filter. A typical first order high pass filter is shown below:

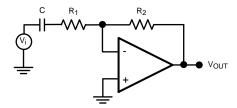


Figure 46. Highpass Filter

Writing the KCL for this circuit:

(V<sub>1</sub> denotes the voltage between C and R<sub>1</sub>)

$$\frac{V_1 - V_i}{\frac{1}{jwC}} = \frac{V_1 - V}{R_1} \tag{14}$$

$$\frac{V^{2}+V_{1}}{R_{1}} = \frac{V^{2}+V_{0}}{R_{2}} \tag{15}$$

Solving these two equations to find the transfer function and using:

$$f_{O} = \frac{1}{2\pi R_{1}C} \tag{16}$$

(high frequency gain)  $^{H_{O}\,=\,\frac{-R_{2}}{R_{1}}}$  and  $^{H\,=\,\frac{V_{O}}{V_{i}}}$ 

Which results:

$$H = H_{O} \frac{j (f/f_{O})}{1 + j (f/f_{O})}$$
(17)

Looking at the transfer function, it is clear that when  $f/f_O$  is small, the capacitor is open and hence no signal is getting in to the amplifier. As the frequency increases the amplifier starts operating. At  $f = f_O$  the capacitor behaves like a short circuit and the amplifier will have a constant, high frequency, gain of  $H_O$ . Figure 47 shows the transfer function of this high pass filter:

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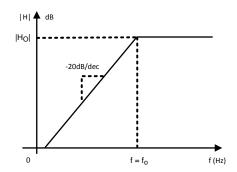


Figure 47. Highpass Filter Transfer Function

#### **BAND PASS FILTER**

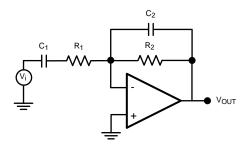


Figure 48. Bandpass Filter

Combining a low pass filter and a high pass filter will generate a band pass filter. In this network the input impedance forms the high pass filter while the feedback impedance forms the low pass filter. Choosing the corner frequencies so that  $f_1 < f_2$ , then all the frequencies in between,  $f_1 \le f \le f_2$ , will pass through the filter while frequencies below  $f_1$  and above  $f_2$  will be cut off.

The transfer function can be easily calculated using the same methodology as before.

$$H = H_{O} \ \frac{j \ (f/f_{1})}{\left[1 + j \ (f/f_{1})\right] \ \left[1 + j \ (f/f_{2})\right]}$$

where

$$f_{1} = \frac{1}{2\pi R_{1}C_{1}}$$

$$f_{2} = \frac{1}{2\pi R_{2}C_{2}}$$

$$H_{O} = \frac{-R_{2}}{R_{1}}$$
(18)

The transfer function is presented in the following figure.



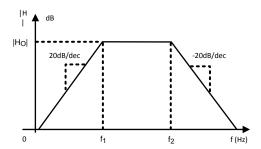


Figure 49. Bandpass filter Transfer Function

#### STATE VARIABLE ACTIVE FILTER

State variable active filters are circuits that can simultaneously represent high pass, band pass, and low pass filters. The state variable active filter uses three separate amplifiers to achieve this task. A typical state variable active filter is shown in Figure 50. The first amplifier in the circuit is connected as a gain stage. The second and third amplifiers are connected as integrators, which means they behave as low pass filters. The feedback path from the output of the third amplifier to the first amplifier enables this low frequency signal to be fed back with a finite and fairly low closed loop gain. This is while the high frequency signal on the input is still gained up by the open loop gain of the 1st amplifier. This makes the first amplifier a high pass filter. The high pass signal is then fed into a low pass filter. The outcome is a band pass signal, meaning the second amplifier is a band pass filter. This signal is then fed into the third amplifiers input and so, the third amplifier behaves as a simple low pass filter.

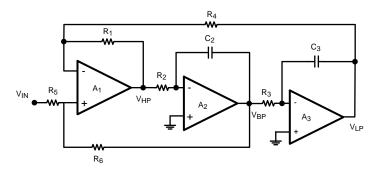
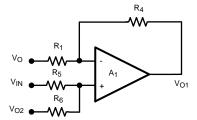


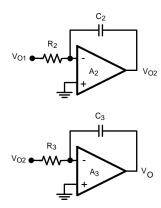
Figure 50. State Variable Active Filter

The transfer function of each filter needs to be calculated. The derivations will be more trivial if each stage of the filter is shown on its own.

The three components are:







For A<sub>1</sub> the relationship between input and output is:

$$V_{O1} = \frac{-R_4}{R_1} V_0 + \left[ \frac{R_6}{R_5 + R_6} \right] \left[ \frac{R_1 + R_4}{R_1} \right] V_{IN} + \left[ \frac{R_5}{R_5 + R_6} \right] \left[ \frac{R_1 + R_4}{R_1} \right] V_{O2}$$
(19)

This relationship depends on the output of all the filters. The input-output relationship for  $A_2$  can be expressed as:

$$V_{O2} = \frac{-1}{s C_2 R_2} V_{O1}$$
 (20)

And finally this relationship for A<sub>3</sub> is as follows:

$$V_{O} = \frac{-1}{s \, C_{3} R_{3}} \, V_{O2} \tag{21}$$

Re-arranging these equations, one can find the relationship between  $V_O$  and  $V_{IN}$  (transfer function of the lowpass filter),  $V_{O1}$  and  $V_{IN}$  (transfer function of the bandpass filter), and  $V_{O2}$  and  $V_{IN}$  (transfer function of the bandpass filter) These relationships are as follows:

#### **Lowpass Filter**

$$\frac{V_{O}}{V_{IN}} = \frac{\left[\frac{R_{1} + R_{4}}{R_{1}}\right] \left[\frac{R_{6}}{R_{5} + R_{6}}\right] \left[\frac{1}{C_{2}C_{3}R_{2}R_{3}}\right]}{s^{2} + s \left[\frac{1}{C_{2}R_{2}}\right] \left[\frac{R_{5}}{R_{5} + R_{6}}\right] \left[\frac{R_{1} + R_{4}}{R_{1}}\right] + \left[\frac{1}{C_{2}C_{3}R_{2}R_{3}}\right]}$$
(22)

#### **Highpass Filter**

$$\frac{V_{O1}}{V_{IN}} = \frac{s^2 \left[ \frac{R_1 + R_4}{R_1} \right] \left[ \frac{R_6}{R_5 + R_6} \right]}{s^2 + s \left[ \frac{1}{C_2 R_2} \right] \left[ \frac{R_5}{R_5 + R_6} \right] \left[ \frac{R_1 + R_4}{R_1} \right] + \left[ \frac{1}{C_2 C_3 R_2 R_3} \right]}$$
(23)

#### **Bandpass Filter**

$$\frac{V_{O2}}{V_{IN}} = \frac{s \left[ \frac{1}{C_2 R_2} \right] \left[ \frac{R_1 + R_4}{R_1} \right] \left[ \frac{R_6}{R_5 + R_6} \right]}{s^2 + s \left[ \frac{1}{C_2 R_2} \right] \left[ \frac{R_5}{R_5 + R_6} \right] \left[ \frac{R_1 + R_4}{R_1} \right] + \left[ \frac{1}{C_2 C_3 R_2 R_3} \right]}$$
(24)



The center frequency and Quality Factor for all of these filters is the same. The values can be calculated in the following manner:

$$\omega_{c} = \sqrt{\frac{1}{C_2 C_3 R_2 R_3}}$$

and

$$Q = \sqrt{\frac{C_2 R_2}{C_3 R_3}} \left[ \frac{R_5 + R_6}{R_6} \right] \left[ \frac{R_1}{R_1 + R_4} \right]$$
 (25)

A design example is shown here:

Designing a bandpass filter with center frequency of 10kHz and Quality Factor of 5.5

To do this, first consider the Quality Factor. It is best to pick convenient values for the capacitors.  $C_2 = C_3 = 1000 pF$ . Also, choose  $R_1 = R_4 = 30 k\Omega$ . Now values of  $R_5$  and  $R_6$  need to be calculated. With the chosen values for the capacitors and resistors, Q reduces to:

$$Q = \frac{11}{2} = \frac{1}{2} \left[ \frac{R_5 + R_6}{R_6} \right] \tag{26}$$

or

$$R_5 = 10R_6 R_6 = 1.5k\Omega R_5 = 15k\Omega$$
 (27)

Also, for f = 10kHz, the center frequency is  $\omega_c = 2\pi f = 62.8$ kHz.

Using the expressions above, the appropriate resistor values will be  $R_2 = R_3 = 16k\Omega$ .

The following graphs show the transfer function of each of the filters. The DC gain of this circuit is:

$$DC GAIN = \left[ \frac{R_1 + R_4}{R_1} \right] \left[ \frac{R_6}{R_5 + R_6} \right] = -14.8 \, dB$$
 (28)

Product Folder Links: SM73308

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## SNOSB90B – JUNE 2011 – REVISED APRIL 2013



# **REVISION HISTORY**

Cł	nanges from Revision A (April 2013) to Revision B	Pa	ge
•	Changed layout of National Data Sheet to TI format		19

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SM73308MG/NOPB	Active	Production	SC70 (DCK)   5	1000   SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08
SM73308MG/NOPB.A	Active	Production	SC70 (DCK)   5	1000   SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08
SM73308MGE/NOPB	Active	Production	SC70 (DCK)   5	250   SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08
SM73308MGE/NOPB.A	Active	Production	SC70 (DCK)   5	250   SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08
SM73308MGX/NOPB	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08
SM73308MGX/NOPB.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	S08

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



# **PACKAGE OPTION ADDENDUM**

www.ti.com 23-May-2025

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 29-Oct-2021

# TAPE AND REEL INFORMATION





A0	
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SM73308MG/NOPB	SC70	DCK	5	1000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
SM73308MGE/NOPB	SC70	DCK	5	250	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
SM73308MGX/NOPB	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3

www.ti.com 29-Oct-2021



#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SM73308MG/NOPB	SC70	DCK	5	1000	208.0	191.0	35.0
SM73308MGE/NOPB	SC70	DCK	5	250	208.0	191.0	35.0
SM73308MGX/NOPB	SC70	DCK	5	3000	208.0	191.0	35.0



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.



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